

Silicon PNP Power Transistors

2SA663

DESCRIPTION

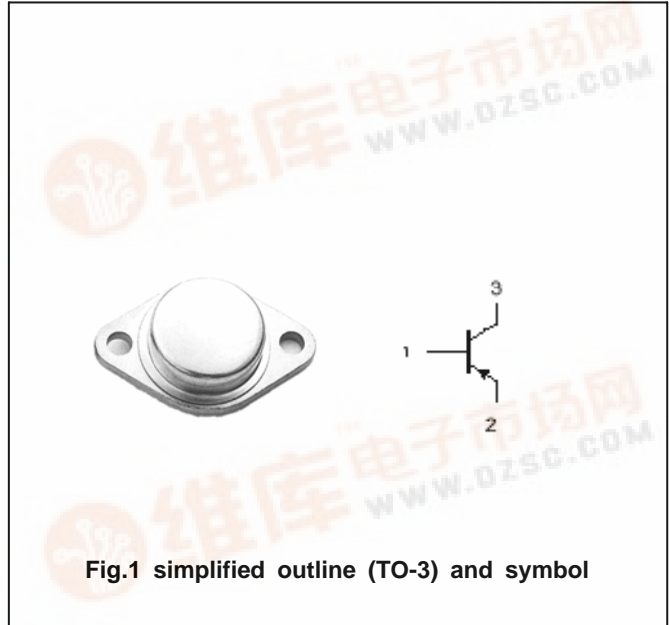
- With TO-3 package
- Wide area of safe operation
- Complement to type 2SC793

APPLICATIONS

- For radio frequency, audio frequency and power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _c	Collector current		-7	A
P _c	Collector power dissipation	T _c =25°C	60	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

Silicon PNP Power Transistors

2SA663

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-100			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-100V ; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V	30		200	
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		6		MHz

Silicon PNP Power Transistors

2SA663

PACKAGE OUTLINE

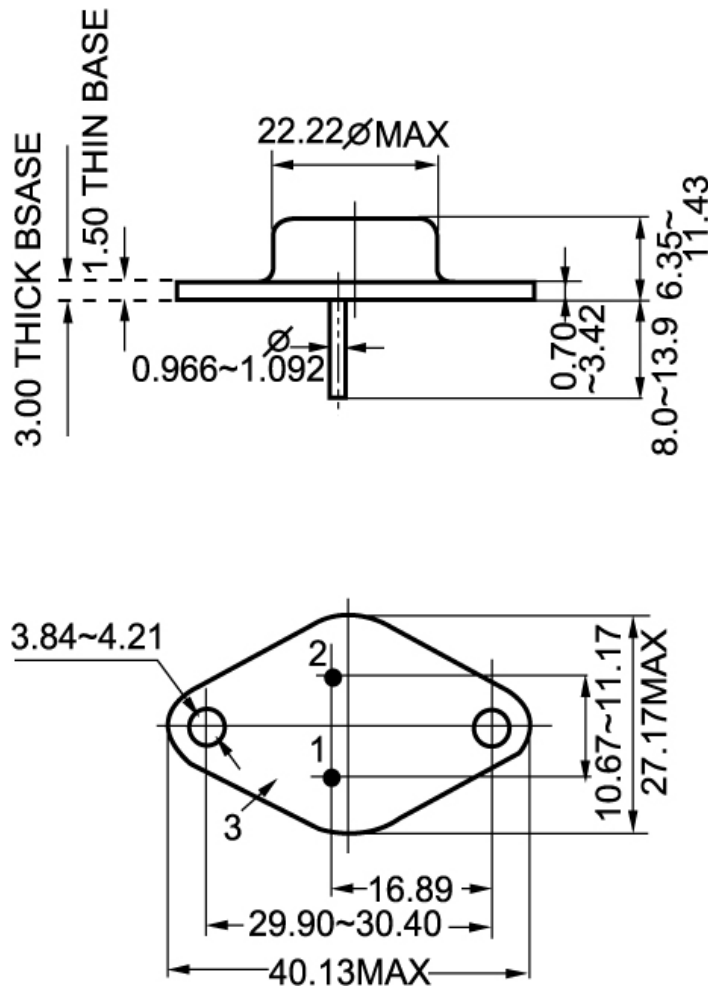


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)